

PATENT
1781-0247P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: Soo Jin CHUA et al. Conf.:
Appl. No.: NEW Group:
Filed: August 5, 2003 Examiner:
For: FORMING INDIUM NITRIDE (INN) AND INDIUM
 GALLIUM NITRIDE (INGAN) QUANTUM DOTS
 GROWN BY METAL-ORGANIC-VAPOR-PHASE-
 EPITAXY (MOCVD)

PRELIMINARY REMARKS

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

August 5, 2003

Sir:

The present application is a divisional application of U.S. application serial number 09/963,616, filed September 27, 2001. During the course of prosecution of the parent application, the Examiner required the filing of a substitute specification. Pursuant to the changes in the rules for submission of amendments effective July 30, 2003, the present application is filed with a substitute specification that incorporates the changes made in the original specification and also includes only the claims to be prosecuted in the present application.

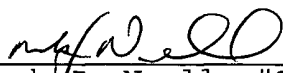
No new matter is introduced into the original application by the substitute specification. For the convenience of the Examiner, a "compare-docs" copy of the specification and claims, showing the differences from the parent application, is attached.

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If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 02-2448 for any additional fee required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

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Attachment: "Comparison" specification